

*Warner-Jenkinson Co. v. Hilton Davis Chemical Co.*, 41 USPQ2d 1865, 1873 (1997).

Please amend the following claims:

(1) Please amend claim 1 as follows:

- D5
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- 1           1. (Thrice Amended) A method for providing a halo implant to a  
2 semiconductor device comprising the steps of:  
3           (a) providing a thin photoresist layer to the semiconductor device that  
4 covers a substantial amount of an active area comprising a source region and a drain  
5 region of the semiconductor device; and  
6           (b) providing the halo implant to the semiconductor device, wherein the  
7 thin photoresist layer is used as a mask.
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(2) Please amend claim 8 as follows:

- D6
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- 1           8. (Fourth Amended) A system for providing a halo implant to a  
2 semiconductor device comprising:  
3           means for providing a thin photoresist layer to the semiconductor device,  
4 wherein the thin photoresist layer covers a substantial amount of an active area  
5 comprising a source region and a drain region of the semiconductor device; and  
6           means for providing the halo implant to the semiconductor device, wherein  
7 the thin photoresist layer is used as a mask.
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IN THE DRAWINGS

A corrected version of Figure 2 is submitted herewith on a separate sheet with corrections marked in red ink. Applicants have labeled element 202 as discussed in the specification and properly labeled element 204 as corresponding to a source region rather than a drain region in semiconductor device 200. Applicants